**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switching mode power supplies.



### 2. Features and benefits

- New 6<sup>th</sup> generation technology
- Low forward voltage drop
- · Low reverse leakage current
- High forward surge capability I<sub>FSM</sub>
- Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

## 3. Applications

- PC/Telecom/Server SMPS
- UPS & energy storage systems
- · Battery formation systems
- EV chargers
- PV inverter and MPPT circuit
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol         | Parameter                       | Conditions  | Notes |              | Values |      | Unit |
|----------------|---------------------------------|---|-------|--------------|--------|------|------|
| Absolute       | maximum rating                  |   |       |              |        |      |      |
| $V_{RRM}$      | repetitive peak reverse voltage |   |       |              | 650    |      | V    |
| I <sub>F</sub> | continuous forward current      | T <sub>mb</sub> ≤ 130 °C, DC; <u>Fig. 2</u>   |       | 50           |        | А    |      |
| T <sub>j</sub> | junction temperature            |   |       | -55 to 175 ° |        | °C   |      |
| Symbol         | Parameter                       | Conditions  | Notes | Min          | Тур    | Max  | Unit |
| Static ch      | aracteristics                   |   |       |              |        |      |      |
| V <sub>F</sub> | forward voltage                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  |       | -            | 1.38   | 1.55 | V    |
|                |                                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   |       | -            | 1.60   | 1.80 | V    |
| Dynamic        | characteristics                 |   |       |              |        |      |      |
| Q <sub>r</sub> | recovered charge                | $I_F = 50 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 7 |       | -            | 84     | -    | nC   |

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol                                    |
|-----|--------|-------------------------------------|--------------------|---|
| 1   | K      | cathode                             |                    | V 1/1 A   |
| 2   | А      | anode                               |                    | K <del>-                                   </del> |
| mb  | mb     | mounting base; connected to cathode | TO247-2L           |   |

## 6. Ordering information

#### **Table 3. Ordering information**

| Type number  | Package  | Orderable part number | Packing | Small packing | Package   | Package     |
|--------------|----------|-----------------------|---------|---------------|-----------|-------------|
|              | name     |                       | method  | quantity      | version   | issue date  |
| WNSC6D50650W | TO247-2L | WNSC6D50650W6Q        | Tube    | 30            | TO247P-2L | 09-Mar-2023 |

# 7. Marking

### Table 4. Marking codes

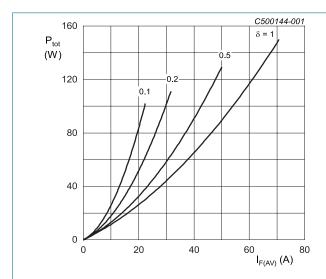
| Type number  | Marking codes    |
|--------------|------------------|
| WNSC6D50650W | WNSC6D<br>50650W |

# 8. Limiting values

**Table 5. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions   | Notes | Values     | Unit             |
|------------------|---------------------------------|--|-------|------------|------------------|
| $V_{RRM}$        | repetitive peak reverse voltage |  |       | 650        | V                |
| $V_{\text{RWM}}$ | crest working reverse voltage   |  |       | 650        | V                |
| $V_R$            | reverse voltage                 | DC   |       | 650        | V                |
| I <sub>F</sub>   | continuous forward              | T <sub>mb</sub> ≤ 130 °C, DC; <u>Fig. 2</u>  |       | 50         | А                |
|                  | current                         | T <sub>mb</sub> ≤ 125 °C, DC; <u>Fig. 2</u>  |       | 54         | Α                |
|                  |                                 | T <sub>mb</sub> ≤ 25 °C, DC; <u>Fig. 2</u>   |       | 110        | Α                |
| I <sub>FRM</sub> | repetitive peak forward current | $\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 125 °C;<br>square-wave pulse |       | 85         | А                |
| I <sub>FSM</sub> | non-repetitive peak             | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                                  |       | 320        | Α                |
|                  | forward current                 | $t_p$ = 10 $\mu$ s; $T_{j(init)}$ = 25 °C; square-wave pulse                           |       | 1880       | Α                |
| l <sup>2</sup> t | I <sup>2</sup> t for fusing     | sine-wave pulse; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms                                  |       | 512        | A <sup>2</sup> s |
| T <sub>stg</sub> | storage temperature             |  |       | -55 to 175 | °C               |
| T <sub>j</sub>   | junction temperature            |  |       | -55 to 175 | °C               |



 $I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta}$   $V_o = 0.992 \text{ V; } R_s = 0.0159 \text{ }\Omega$  Fig. 1. Forward power dissipation as a function of average forward current; square waveform;

maximum values

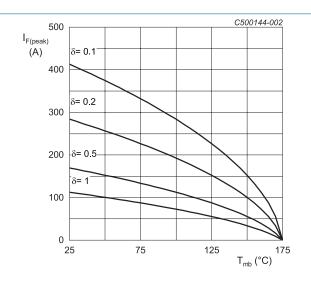
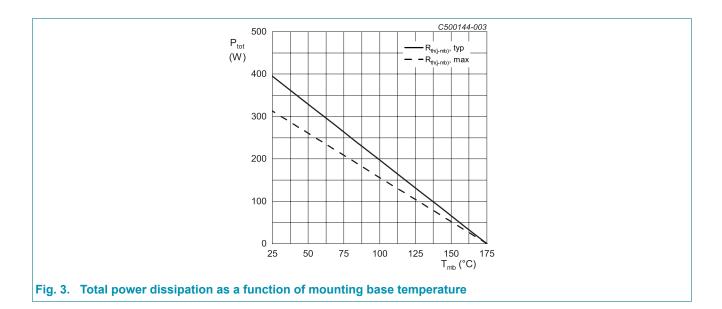


Fig. 2. Current derating as a function of mounting base temperature



### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions  | Notes | Min | Тур  | Max  | Unit |
|-----------------------|--|-------------|-------|-----|------|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | Fig. 4      |       | -   | 0.38 | 0.48 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air |       | -   | 60   | -    | K/W  |

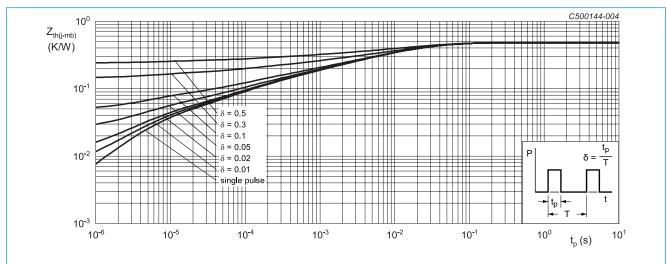
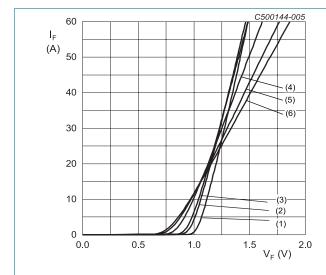


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

**Table 7. Characteristics** 

| Symbol          | Parameter                       | Conditions  | Notes  | Min | Тур  | Max     | Unit |
|-----------------|---------------------------------|---|--------|-----|------|---------|------|
|                 | aracteristics                   |   | 110000 |     | -76  | 1110.24 | 0    |
| V <sub>F</sub>  | forward voltage                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  |        | -   | 1.38 | 1.55    | V    |
|                 |                                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   |        | -   | 1.60 | 1.80    | V    |
|                 |                                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>   |        | -   | 1.70 | 1.90    | V    |
| I <sub>R</sub>  | reverse current                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |        | -   | 5    | 200     | μA   |
|                 |                                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>  |        | -   | 50   | 800     | μA   |
| Dynamic         | characteristics                 |   |        |     |      |         |      |
| $Q_r$           | recovered charge                | $I_F = 50 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |        | -   | 84   | -       | nC   |
| C <sub>d</sub>  | diode capacitance               | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C   |        | -   | 1900 | -       | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C   |        | -   | 226  | -       | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C   |        | -   | 214  | -       | pF   |
| E <sub>as</sub> | non-repetitive avalanche energy | I <sub>R</sub> = 10 A; L = 5 mH; T <sub>j(init)</sub> = 25 °C   |        | 250 | -    | -       | mJ   |



 $V_o$  = 0.992 V;  $R_s$  = 0.0159  $\Omega$ 

(1)  $T_j = -55$  °C; typical values

(2)  $T_j = 0$  °C; typical values

(3)  $T_j = 25$  °C; typical values

(4)  $T_j = 100 \, ^{\circ}\text{C}$ ; typical values

(5)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values

(6) T<sub>j</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

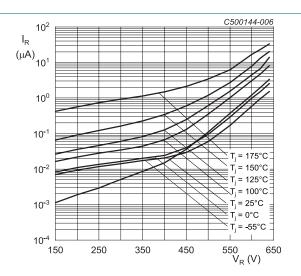


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

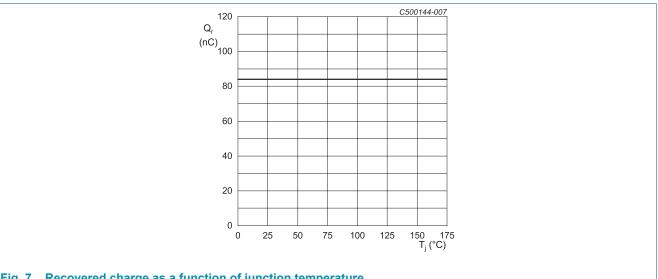
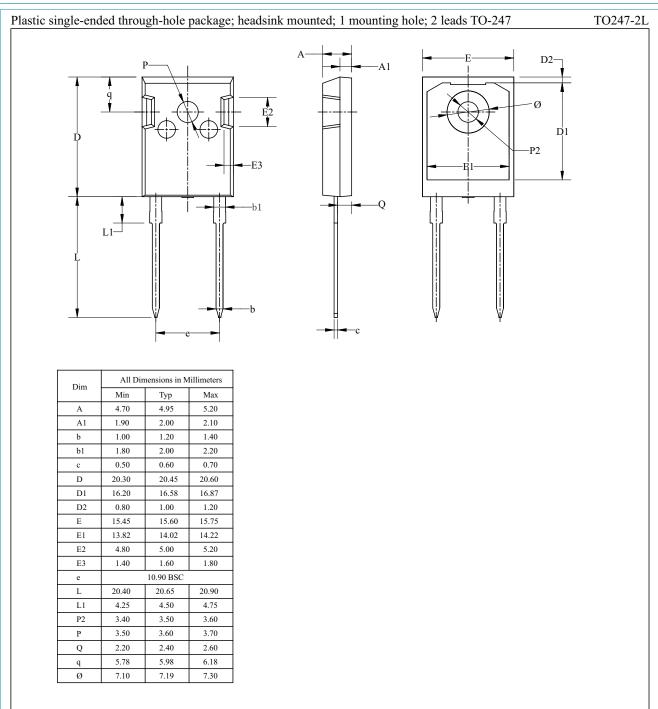


Fig. 7. Recovered charge as a function of junction temperature

# 11. Package outline



## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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